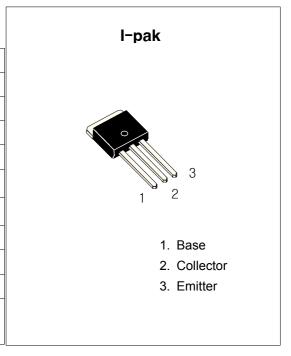


PNP EPITAXIAL SILICON TRANSISTOR

GENERAL PURPOSE AMPLIFIER

- ♦ Low Speed Switching
- ♦ Complement to WSC752

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)						
Characteristic	Symbol	Value	Unit			
Collector-Base Voltage	Vсво	-40	V			
Collector-Emitter Voltage	VCEO	-30	V			
Emitter-Base voltage	VEBO	-5	V			
Collector Current(DC)	Ic	-2	Α			
Collector Current(Pulse)*	Ic	-7	Α			
Base Current	lв	-0.6	Α			
Collector Power Dissipation(Tc=25℃)	Рс	15	W			
Collector Power Dissipation(Ta=25℃)	Pc	1.2	W			
Junction Temperature	Tj	150	$^{\circ}$			
Storage Tomporature	Tota	-55~	J			
Storage Temperature	Tstg	+150				



ELECTRICAL CHARACTERISTICS

(Ta=25℃, unless otherwise specified)

Characteristic	Symbol	Test Condition	Min	TYP	MAX	Unit
Collector-Base Breakdown Voltage	ВУсво	Ic=-100#A ,IE=0	-40			V
Collector-Emitter Breakdown Voltage	BVCEO	Ic=-10mA, I _B =0	-30			V
Emitter-Base Breakdown Voltage	ВУЕВО	Ic=-1mA ,Ic=0	-5			V
Collector Cut-off Current	Ісво	VCB=-40V ,IE=0			-0.1	μA
Emitter Cut-off Current	IEBO	V _{EB} =-5V ,I _C =0			-0.1	μА
*DC Current Gain	#hFE	VCE=-2V, IC=-500mA	100		400	
*Collector-Emitter Saturation Voltage	VCE(sat)(1) VCE(sat)(2)	IC=-2.0A, IB=-200 ^{mA} IC=-1.5A, IB=-30 ^{mA}		-0.5	-0.8 -2	V
Current Gain Bandwith Product	f⊤	VCE=-5V,IC=-500mA		120		MHZ
Output Capacitance	Cob	VCB=-10V ,IE=0 f=1MHZ		13		pF

^{*} Pulse test:PW≤ 350us,Duty cycle≤ 2%

hFE Classification:

Classification	0	Y	G
hfe	100~200	160~320	200~400

^{*}PW≤ 10ms,Duty Cycle≤ 50%

